

# M52042FP NTSC Video Chroma Signal Processor

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#### Description

The M52042FP is a semiconductor integrated circuit (IC) for picture signal processing that has been developed for NTSC system LCD color TV.

This IC has a built-in luminance signal processing circuit and color signal processing circuit, which is employed to convert a composite video signal to an RGB signal.

### Features

- Low voltage and low power dissipation design
- Built-in Y/C separation circuit and external chroma trap switchable (fc is nearly equal to 1.5 MHz.)
- Built-in sync separation circuit
- Provided with Y-signal blanking function by HD pulse
- R.G.B. signal output
- Tint, contrast, picture quality and color control linearly adjustable
- 24-pin, shrink pitch, flat package employed
- Same package as in PAL system video chroma IC M52045FP, pin perfectly compatible

### Application

LCD color TV and LCD color view finder

#### **Recommended Operating Condition**

Supply voltage range: 3.7 to 4.5 V

Rated supply voltage: 4.0 V



### **Block Diagram**



#### **Pin Arrangement**





## **Pin Description**

Pin No.	Name	Peripheral Circuit of Pins				
1	VIDEO IN (Video input)	1 Vcc Bias GND				
2	SYNC SEP IN (SYNC separation input)	② ↓ ↓ Bias GND				
3	ACC FILTER	W W 47 K S GND 3				
4	SYNC OUT (SYNC separation output)	Vcc ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓				
5	HD IN (HD pulse input)	50 K 50 K GND				



Pin No.	Name	Peripheral Circuit of Pins
6	PED CLAMP C	(6)
	(Pedestal-clamped capacitance)	
		<b>≥</b> 9 k2
		Bias
		₹ \$5 k
-		
1	CHROMA TRAP	
		V <sub>CC</sub>
		GND
8	YOUT	
	(Y output)	₹ \$150 k \$40 k
		GND
9	CONTRAST CONT.	
	(Contrast control)	5 k 👌 👌 k
		≥36 k
		\$30 k
		GND
10	R OUT	V <sub>cc</sub>
	(R oulpul)	20 K ≥ 20 K
11	GOUT	
	(G output)	
12	BOUT	Bias —
	(B output)	≩ ≩360
		GND
13	GND (Grounding)	
24	V <sub>CC</sub> +4 V (Power supply)	—



Pin No.	Name	Peripheral Circuit of Pins
16	S.W.	(16) V <sub>CC</sub>
	(Selector switch)	× 5175 k
22	VCXO MONITOR	Z2 X X X X X X X X X X X X X
14	PIX CONT. (Picture quality control)	14 V <sub>CC</sub> V <sub>CC</sub> 14 100 k 100 k 1
15	KILLER OUT (Killer output)	100 k 15 100 k 15 100 k 150 k
17	APC FILTER	10 k 10 k (17) GND



Pin No.	Name	Peripheral Circuit of Pins
18	KILLER FILTER	41 k 41 k 18 GND
19	TINT CONT. (Tint control)	V <sub>CC</sub> 15 k 15 k 15 k 160 k Bias 160 k 19 19 GND
20	COLOR (Color control)	
21	VCXO IN (VCXO input)	22 k $22 k$ $30 k$ $30 k$ $Bias$ $22 k$ $22 k$ $GND$
23	VCXO OUT (VCXO output)	V <sub>CC</sub> 500 1 k 15 k Bias 180 GND



## **Absolute Maximum Ratings**

Item	Symbol	Ratings	Unit
Supply voltage	V <sub>CC</sub>	4.8	V
Power dissipation	Pd	680	mW
Operating temperature	Topr	-10 to 70	°C
Storage temperature	Tstg	-45 to 120	°C
Thermal derating	Κθ	5.4	mW/°C
Electrostatic capacity	Vmax	±200*	V

Note: Charging capacity: 200 pF





### **Electrical Characteristics**

 $(Ta = 25^{\circ}C, unless otherwise noted)$ 

						Teet	(
ltem	Symbol	Min	Тур	Мах	Unit	No	Test Conditions
Circuit current	I <sub>CC</sub>	_	17	21	mA	1	Input standard color bar signal of $V_{CC} = 4 V$ .
SYNC SEP section							
SYNC tip voltage	Vsync 1	2.20	2.30	2.40	V	2	Measure each output signal SYNC tip
	Vsync 7	1.25	1.40	1.50			bar signal of 0.7 Vp-p is input.
SYNC output amplitude	Vsync H	2.7	3.1	3.4	Vр-р	3	Input only SYNC pulse of pulse width 4.7 $\mu$ s to pin (1). Measure the output amplitude at
	Vsync L	2.7	3.1	3.4			pin (4) when the input SYNC pulse amplitudes are 0.2 and 0.05 Vp-p.
SYNC output pulse width	Tsync H	3.7	4.7	5.7	μS	4	Input only SYNC pulse of pulse width 4.7µs to pin (1). Measure the output amplitude at pin (4) when the input SYNC pulse amplitudes are 0.2 and 0.05 Vp-p.
	Tsync L	3.7	4.7	5.7			
SYNC output pulse delay	Dsync H	3.7	4.7	6.0	μS	5	Input only SYNC pulse of pulse width $4.7\mu s$ to pin (1). Measure the pulse width + delay
	Dsync L	3.7	4.7	6.0			time when the input SYNC pulse amplitudes are 0.2 and 0.05 Vp-p.
Video section	1		1				
YLPF frequency characteristics	YLPF (L)	1.45	1.55		MHz	6	Measure the frequency at which the sine wave output amplitude is -3 dB when the
(Pin (7) )	YLPF (H)	-30	-24	-21	dB		input signal ( ∭∭∭∬∐[0.2 ∨p-p ) 0.2 Vp-p
							is input. Also measure the output gain at input sine wave 3.58 MHz.
YLPF frequency	YLPF	5.0	7.0	10.0	MHz	7'	Measure the frequency at which the sine
characteristics	through						wave output amplitude is -3 dB when the
(through mode)							input signal ( ՈՈՈՈՈՈՈ ፲ ₀.₂ ∨թ-թ_) 0.2 ∨p-p
							is input and V16 is 4.0 $V_{PC}$ input
Maximum	Ymax	11	17	17	Vn-n	7	Input standard staircase wave of 0.7 Vp-p
output	THUX		1.7	1.7	VP P	,	Measure the output amplitude at pin (12) when V9 is 0 V.
Video amplifier	GYmax	4.0	6.0	8.0	dB	8	Input standard staircase wave of 0.7 Vp-p.
gain							Calculate the ratio between the output
							amplitude at pin (12) and input amplitude
O and the set of a set to a l	Matra at (4)	4.00	0.45	4.50	JD		when V9 is 1.7 V.
characteristics	Yctrast (1)	1.20	2.45	4.50	dB 9	9	and calculate the ratio of the input amplitude to the output amplitude in Test No.8 above
	Yctrast (2, 5)	-7.3	-5.0	-2.7			
	Yctrast (3, 5)	_	-30	-17			when V9 is changed 1 V, 2.5 V and 3.5 V.
PIX control characteristics	XPIX (4)	-3.5	-2.0	-0.5	dB	10	Input 1.5 MHz sine wave of 0.2 Vp-p to the input. Measure each output amplitude at pin
							(12) when V9 is 1.7 V, and V14 is changed
	XPIX (0)	10.0	12.0	14.0	dB		to 2, 4 and 0 V and calculate the ratio
							amplitude when $V14 = 2$ V.
Y AMP gain	GYmap	9.1	11.0	12.6	dB	11	Input standard staircase wave of 0.7 Vp-p
							and calculate the ratio between the output amplitude at pin (8) and input amplitude.
PED offset level	Vped	0.00	0.05	0.06		12	With input SYNC pulse at 0.2 Vp-p, measure
							pin (12) output pedestal offset, and calculate ratio of the offset to that when $0.7 \text{ Mp}_{-}$
							standard staircase is input.



# **Electrical Characteristics (cont.)**

ltem	Symbol	Min	Typ	Max	Unit	Test No	Test Conditions
Chroma section							
Acc control characteristics	Cacc (+4)	0	0.7	1.5	dB	14	Input burst 0.2 Vp-p + CW 4.33 MHz shall be 0 dB. Measure the output at pin (12)
	Cacc (-20)	-6.0	-2.0	0			dB, and calculate the ratio of the measured amplitude to the output amplitude at 0 dB.
Killer operation	Ckilr	-53	-49	-43	dB	15	Input a chroma signal of 0.2 Vp-p to the input. Reduce the amplitude and measure the amplitude ratio when the voltage at pin (15) exceeds 2.5 V.
Color control	Cast (4)	2	2.2	4.5	dB	16	Input burst 0.2 Vp-p + CW 4.33 MHz, change V20 to 2 V 4 V 3 V 1 V and 0 5 V
Characteristics	Cast (3)	1.5	2.0	4.0			to measure each output (100 kHz beat) amplitude at pin (12), and calculate the ratio
	Cast (1)	-8.5	-6	-4			
	Cast (0, 5)	-17	-13	-10			output amplitude at $V20 = 1 V$ .
APC pull-in range	∆fapc	+400	+600	_	Hz	17	Input only SYNC, and after adjusting free run, input 0.2 Vp-p
			-300	-200			the frequency. Measure the frequency when VCXO oscillator is placed in a locked condition from the free-run condition.
B demodulator sensitivity	DB	0.8	1.2	1.6	Vp-р	18	Input CW 4.33 MHz of 0.2 Vp-p to the input, and measure the output amplitude at pin (12) when V20 = 1 V.
Demodulated output voltage	R (R/B)	0.46	0.52	0.60	—	19	Input CW 4.33 MHz of 0.2 Vp-p to the input, measure the output amplitude at pins (10), (11) when $\sqrt{20} = 1 V$ and calculate the ratio
	R (G/B)	0.20	0.30 0.40			of the measured amplitude to the output amplitude in Test No.18 above.	
Killer output voltage H	Vkiller H	2.5	3.2	—	V	21	Measure DC voltage at pin (15) when 0 V and 4 V are applied to pin (18).
Killer output voltage L	Vkiller L	—	0.20	0.40			
TINT control variance	Т	75	85	100	deg	22	Input a chroma signal of 0.4 Vp-p to the input, and measure the phase variance at pin (12) when 0 V and 4 V are applied to V19.
TINT control characteristics	Topen	-5	+5	+15	deg	23	Apply B monochromatic wave, (variable phase) 0.4 Vp-p and burst 0.2 Vp-p to the input. Measure the input phase in which the output at pin (12) becomes maximum with V19 open as burst phase –180 degrees.
	Tmin	-55	40	-25	deg		Apply B monochromatic wave (variable phase) 0.4 Vp-p and burst 0.2 Vp-p to the input. Measure the input phase in which the
	Tmax	+30	-40	+60			output at pin (12) becomes "maximum" when V19 is 0 V and 4 V as burst phase -180 degrees.
HD for chroma delay	Dhd	—	2.0	2.2	μS	24	Apply B monochromatic wave 0.4 Vp-p and burst 0.2 Vp-p to the input. Measure the delay time from HD pulse rise to the chroma rise of pin (12) output.



### Input Signal



### **Test Circuit**



### **Application Example**





### **Package Dimensions**





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